NPN SILICON HIGH FREQUENCY TRANSISTOR

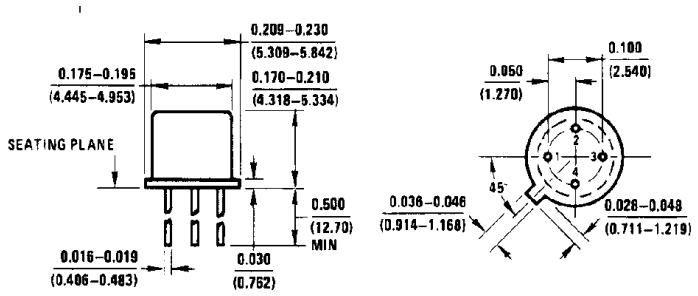
DESCRIPTION:

The **2N3570** is Designed for High Frequency Low Noise Amplifier and Oscillator Applications.

MAXIMUM RATINGS

I_C	50 mA
V_{CB}	30 V
V_{CE}	15 V
V_{EB}	3.0 V
P_{DISS}	200 mW @ T_C = 25 ^{O}C
T_J	-65 ^{O}C to +200 ^{O}C
T_{STG}	-65 ^{O}C to +200 ^{O}C
θ_{JC}	500 ^{O}C/W

PACKAGE STYLE TO- 72



1 = EMITTER 2 = BASE
3 = COLLECTOR 4 = CASE

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 2 mA	15			V
BV_{CBO}	I_C = 1.0 μA	30			V
I_{CBO}	V_{CB} = 6.0 V			10	μA
	T_A = 150 ^{O}C			1.0	
BV_{EBO}	I_E = 10 μA	3.0			V
h_{FE}	V_{CE} = 6.0 V I_C = 5.0 mA	20		150	---
C_{ob}	V_{CB} = 6 V f = 1.0 MHz			0.75	pF
h_{FE}	V_{CE} = 6 V I_C = 5 mA	20		150	---
$\lvert h_{fe} \rvert$	V_{CE} = 6 V I_C = 5 mA f = 400 MHz	3.75	4.25	6	---
$r_b{'}C_C$	V_{CB} = 6 V I_E = -5 mA f = 79.8 MHz	1	5	8	pF
P_{OSC}	V_{CC} = 20 V I_C = 15 mA f = 1.0 GHz		60		mW
N_F	V_{CB} = 6 V I_C = 2 mA R_G = 50 Ω f = 1.0 GHz		6	7	dB

Specifications are subject to change without notice.